

## 2<sup>nd</sup> Generation thinQ!<sup>TM</sup> SiC Schottky Diode

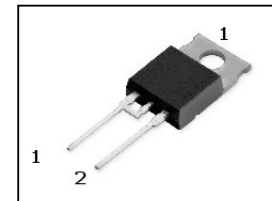
### Features

- Revolutionary semiconductor material - Silicon Carbide
- No reverse recovery/ no forward recovery
- Temperature independent switching behavior
- High surge current capability
- Qualified according to JEDEC<sup>1)</sup> for target applications
- Breakdown voltage tested at 5mA<sup>2)</sup>
- Optimized for high temperature operation

### Product Summary

$V_{DC}$	600	V
$Q_c$	3.2	nC
$I_F$	2	A

PG-TO220-2-2



thinQ! 2G Diode specially designed for fast switching applications like:

- CCM PFC

Type	Package	Marking	Pin 1	Pin 2
IDT02S60C	PG-TO220-2-2	D02S60C	C	A

### Maximum ratings

Parameter	Symbol	Conditions	Value	Unit
Continuous forward current	$I_F$	$T_C < 120\text{ °C}$	2	A
		$T_C < 70\text{ °C}$	3	
RMS forward current	$I_{F,RMS}$	$f=50\text{ Hz}$	2.8	
Surge non-repetitive forward current, sine halfwave	$I_{F,SM}$	$T_C=25\text{ °C}, t_p=10\text{ ms}$	11.5	
		$T_C=150\text{ °C}, t_p=10\text{ ms}$	9.7	
Repetitive peak forward current	$I_{F,RM}$	$T_j=150\text{ °C},$ $T_C=100\text{ °C}, D=0.1$	7.3	
Non-repetitive peak forward current	$I_{F,max}$	$T_C=25\text{ °C}, t_p=10\text{ }\mu\text{s}$	100	
$i^2t$ value	$\int i^2 dt$	$T_C=25\text{ °C}, t_p=10\text{ ms}$	0.61	A <sup>2</sup> s
		$T_C=150\text{ °C}, t_p=10\text{ ms}$	0.44	
Repetitive peak reverse voltage	$V_{RRM}$	$T_j=25\text{ °C}$	600	V
Diode dv/dt ruggedness	dv/dt	$V_R = 0 \dots 480\text{V}$	50	V/ns
Power dissipation	$P_{tot}$	$T_C=25\text{ °C}$	18	W
Operating and storage temperature	$T_j, T_{stg}$		-55 ... 175	°C
Mounting torque		M3 and M3.5 screws	60	Mcm

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Thermal characteristics**

Thermal resistance, junction - case	$R_{thJC}$		-	-	8.5	K/W
Thermal resistance, junction - ambient	$R_{thJA}$	leaded	-	-	62	
Soldering temperature, wavesoldering only allowed at leads	$T_{sold}$	1.6mm (0.063 in.) from case for 10s	-	-	260	°C

**Electrical characteristics**
**Static characteristics**

DC blocking voltage	$V_{DC}$	$I_R=0.05mA, T_j=25^\circ C$	600	-	-	V
Diode forward voltage	$V_F$	$I_F=2 A, T_j=25^\circ C$	-	1.7	1.9	
		$I_F=2 A, T_j=150^\circ C$	-	2.1	2.6	
		$I_F=3 A, T_j=25^\circ C$	-	2.1	2.4	
		$I_F=3 A, T_j=150^\circ C$	-	2.8	3.7	
Reverse current	$I_R$	$V_R=600 V, T_j=25^\circ C$	-	0.23	15	µA
		$V_R=600 V, T_j=150^\circ C$	-	1	150	

**AC characteristics**

Total capacitive charge	$Q_c$	$V_R=400 V, I_F \leq I_{F,max}, di_F/dt=200 A/\mu s,$	-	3.2	-	nC
Switching time <sup>3)</sup>	$t_c$	$T_j=150^\circ C$	-	-	<10	ns
	$C$	$V_R=1 V, f= MHz$	-	60	-	pF
		$V_R=300 V, f=1 MHz$	-	8	-	
		$V_R=600 V, f=1 MHz$	-	8	-	

<sup>1)</sup> J-STD20 and JESD22

<sup>2)</sup> All devices tested under avalanche condition, for a time periode of 5ms, at 5mA.

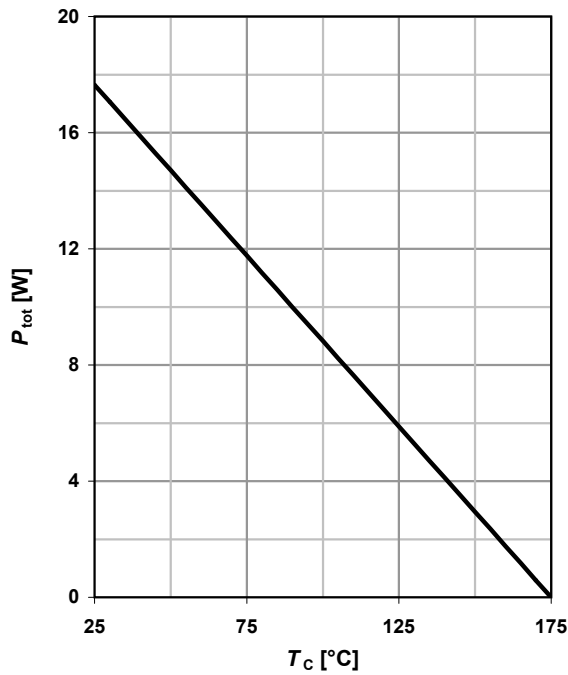
<sup>3)</sup>  $t_c$  is the time constant for the capacitive displacement current waveform (independent from  $T_j, I_{LOAD}$  and  $di/dt$ ), different from  $t_{rr}$ , which is dependent on  $T_j, I_{LOAD}, di/dt$ . No reverse recovery time constant  $t_{rr}$  due to absence of minority carrier injection.

<sup>4)</sup> Only capacitive charge occurring, guaranteed by design.

**1 Power dissipation**

$$P_{tot} = f(T_C)$$

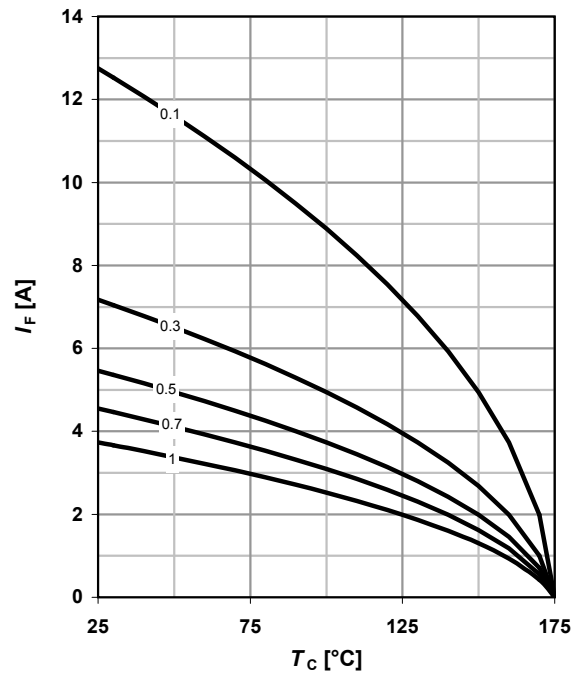
parameter:  $R_{thJC(max)}$



**2 Diode forward current**

$$I_F = f(T_C); T_j \leq 175 \text{ °C}$$

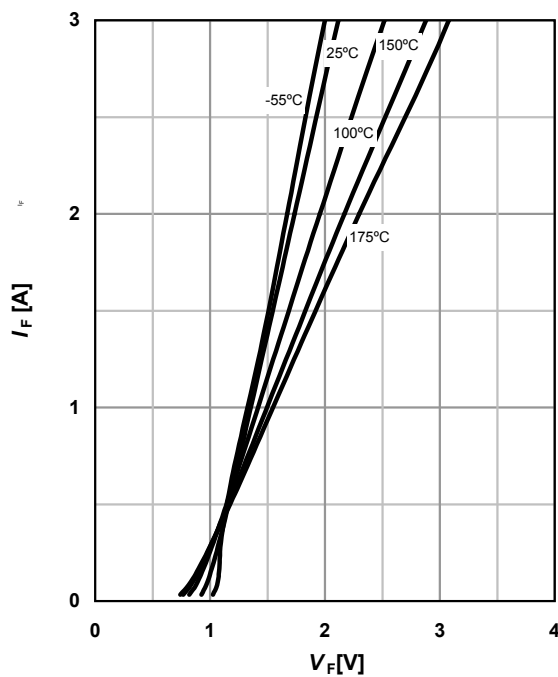
parameter:  $D = t_p / T$



**3 Typ. forward characteristic**

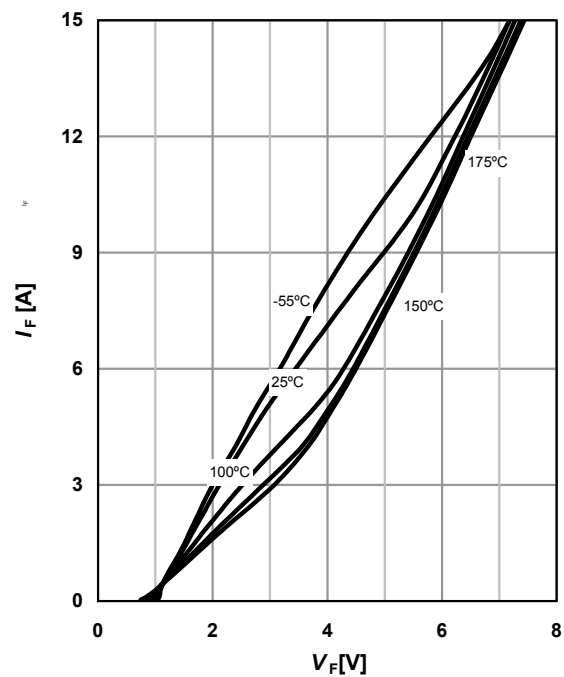
$$I_F = f(V_F); t_p = 400 \text{ } \mu\text{s}$$

parameter:  $T_j$



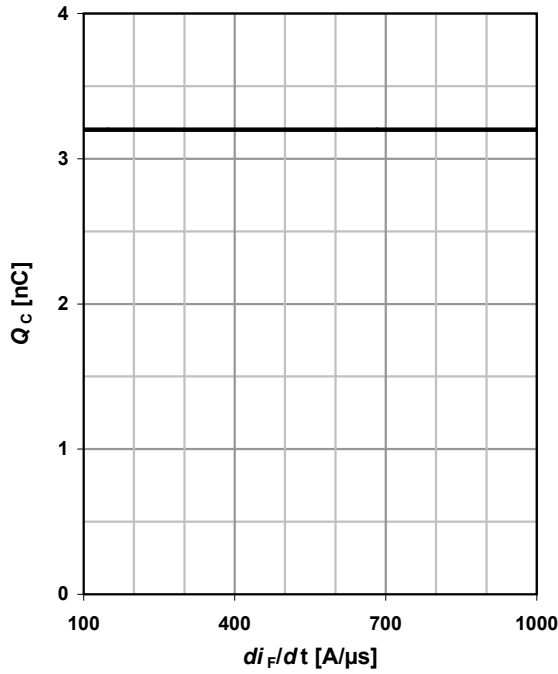
**4 Typ. forward characteristic in surge current mode**

$$I_F = f(V_F); t_p = 400 \text{ } \mu\text{s}; \text{ parameter: } T_j$$



**5 Typ. capacitance charge vs. current slope**

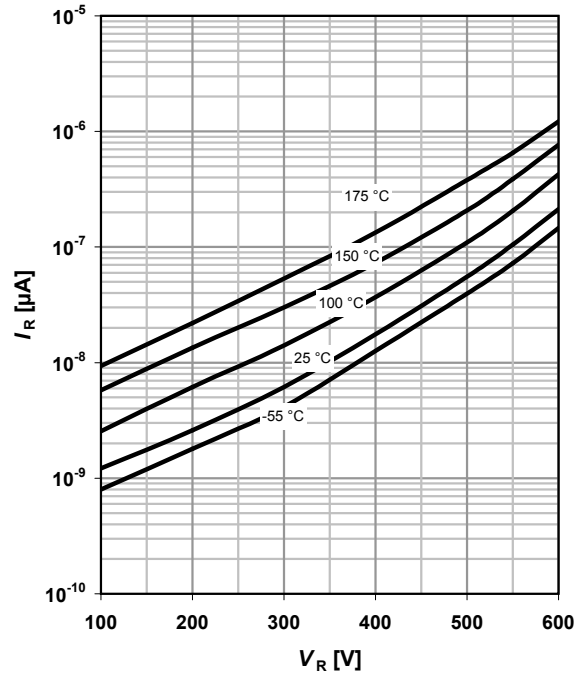
$Q_C = f(di_F/dt^4); T_J = 150\text{ }^\circ\text{C}; I_F \leq I_{F,max}$



**6 Typ. reverse current vs. reverse voltage**

$I_R = f(V_R)$

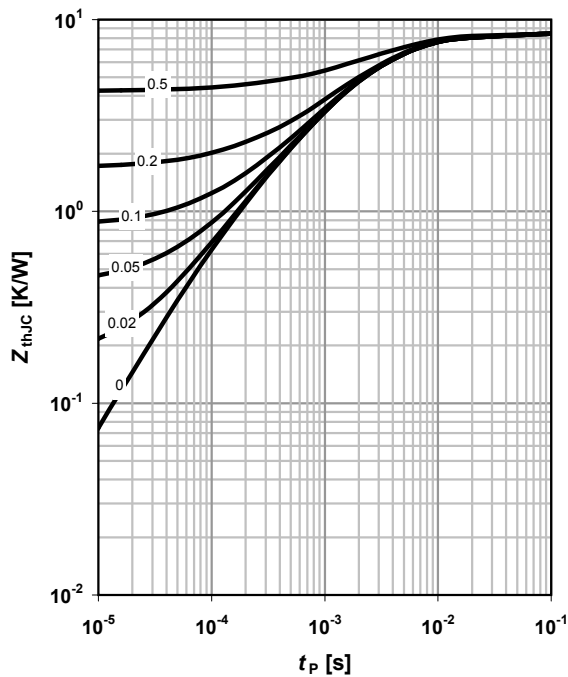
parameter:  $T_J$



**7 Transient thermal impedance**

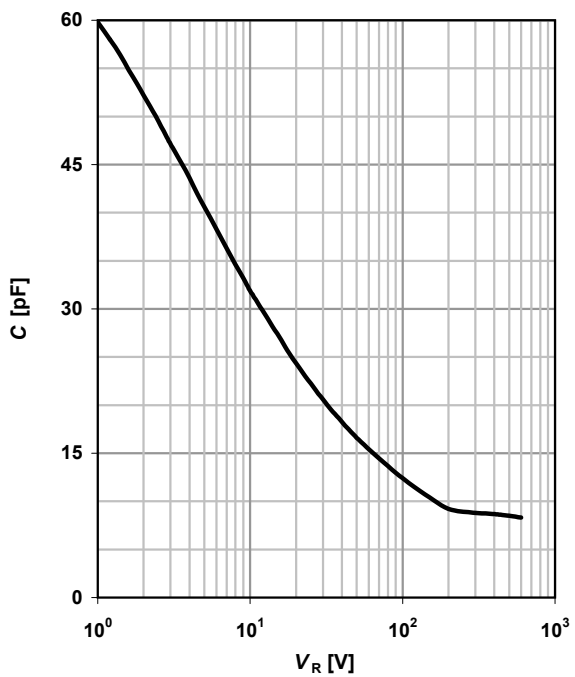
$Z_{thJC} = f(t_p)$

parameter:  $D = t_p/T$



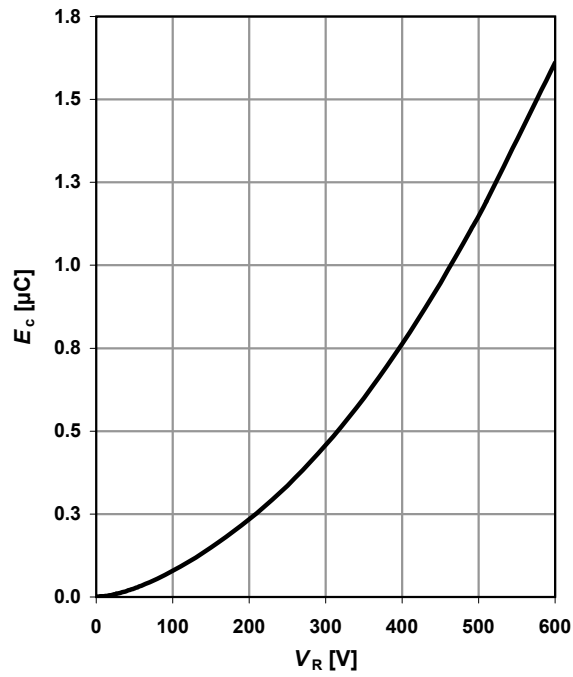
**8 Typ. capacitance vs. reverse voltage**

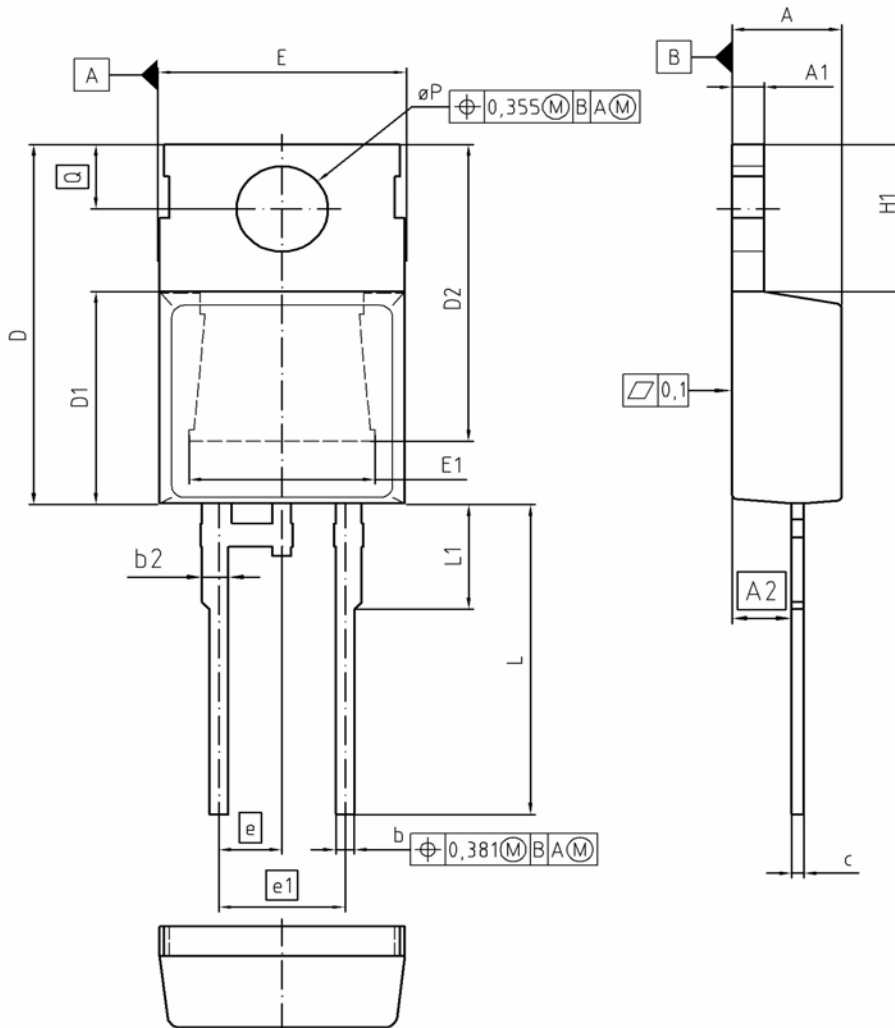
$C = f(V_R); T_C = 25\text{ }^\circ\text{C}, f = 1\text{ MHz}$



**9 Typ. C stored energy**

$$E_C = f(V_R)$$



**Package Outline:PG-TO220-2-2**


DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.191	4.699	0.165	0.185
A1	1.170	1.400	0.046	0.055
A2	2.215	2.718	0.087	0.107
b	0.635	0.889	0.025	0.035
b2	0.950	1.651	0.037	0.065
c	0.330	0.635	0.013	0.025
D	14.808	15.950	0.583	0.628
D1	8.509	9.450	0.335	0.372
D2	12.850	14.245	0.506	0.561
E	9.677	10.363	0.381	0.408
E1	6.500	8.788	0.256	0.346
e	2.540		0.100	
e1	5.080		0.200	
N	2		2	
H1	5.900	6.900	0.232	0.272
L	12.700	14.000	0.500	0.551
L1	3.048	4.800	0.120	0.189
øP	3.550	3.886	0.140	0.153
Q	2.540	3.048	0.100	0.120

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